

Silicon NPN Power Transistors

3DD201

DESCRIPTION

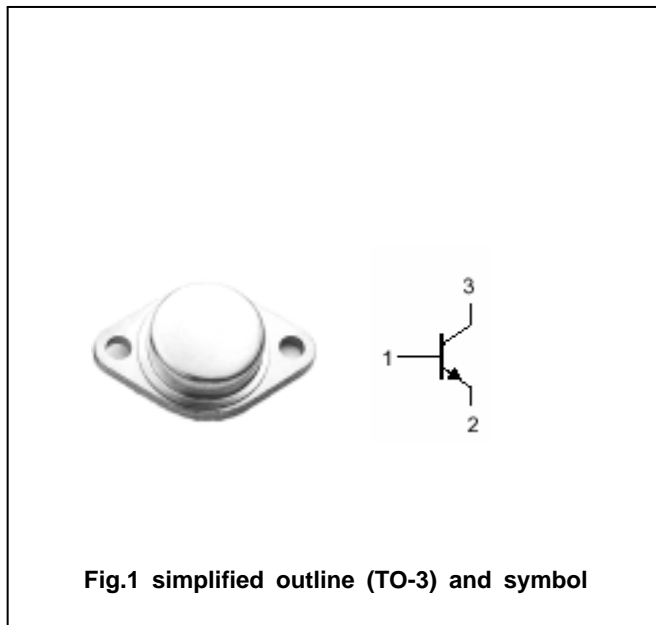
- With TO-3 package
- High collector-base breakdown voltage
: $V_{CBO}=350V$

APPLICATIONS

- For TV horizontal output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	350	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		8	A
P_C	Collector power dissipation	$T_C=25$	50	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

THERMAL CHARACTERISTICS

SYMBOL	CHARACTERISTICS	MAX	UNIT
R_{jc}	Thermal resistance junction to case	1.5	/W

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CHARACTERISTICS

 $T_j=25$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA ; I_B=0$	150			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	350			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A ; I_B=0.5A$			1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A ; I_B=0.5A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=350V ; I_E=0$			0.5	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=2A ; V_{CE}=10V$	40		120	

PACKAGE OUTLINE

